TECHNICAL DATA DATA SHEET 786, REV. A

SILICON SCHOTTKY RECTIFIER Very Low Forward Voltage Drop

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings

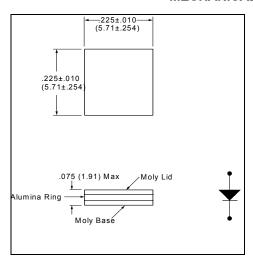
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	30	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	1020	Α
Non-Repetitive Avalanche Energy	E _{AS}	T _J = 25 °C, I _{AS} = 11.5 A, L = 11.5 mH	13	mJ
Repetitive Avalanche Current	I _{AR}	I_{AS} decay linearly to 0 in 1 μ s f limited by T_J max V_A =1.5 V_R	1.5	A
Maximum Thermal Resistance	$R_{ heta JC}$			°C/W
Max. Junction Temperature	T_J	-	-55 to +150	°C
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C

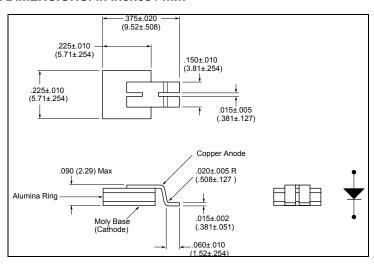
Electrical Characteristics

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 15A, Pulse, T _J = 25 °C	0.60	V
	V_{F2}	@ 15A, Pulse, T _J = 125 °C	0.56	V
Max. Reverse Current	I _{R1}	@V _R = 60V, Pulse,	0.8	mA
		T _J = 25 °C		
	I_{R2}	@V _R = 60V, Pulse,	45	mA
		T _J = 125 °C		
Max. Junction Capacitance	C_T	$@V_R = 5V, T_C = 25 ^{\circ}C$	720	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

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MECHANICAL DIMENSIONS: In Inches / mm





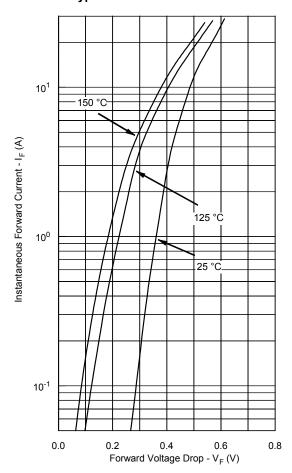
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Typical Forward Characteristics



Typical Reverse Characteristics

